

isc Silicon NPN Power Transistor

2SC4744

DESCRIPTION

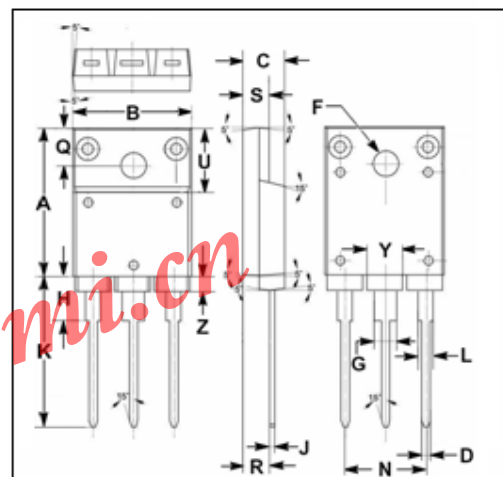
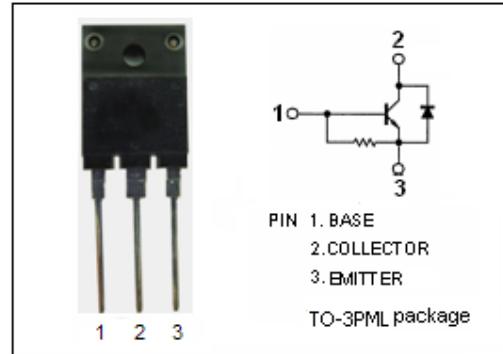
- High Breakdown Voltage-
: $V_{CBO}=1500V$ (Min)
- High Switching Speed
- Built-in Damper Diode

APPLICATIONS

- Designed for character display horizontal deflection output stage applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage	1500	V
V_{EBO}	Emitter-Base Voltage	6	V
$I_{C(peak)}$	Collector Current-Peak	7	A
$I_{C(surge)}$	Collector Current-Surge	16	A
I_D	C-E Diode Forward Current	7	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	50	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.90	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.10
H	5.90	6.10
J	0.595	0.605
K	22.30	22.50
L	1.90	2.10
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.40
U	9.90	10.10
Y	4.70	4.90
Z	1.90	2.10

isc Silicon NPN Power Transistor**2SC4744****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=400\text{mA}$; $I_C=0$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}$; $I_B=1.25\text{A}$			2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=5\text{A}$; $I_B=1.25\text{A}$			1.5	V
I_{CES}	Collector Cutoff Current	$V_{CE}=1500\text{V}$; $R_{BE}=0$			500	μA
h_{FE}	DC Current Gain	$I_C=1\text{A}$; $V_{CE}=5\text{V}$			25	
V_{ECF}	C-E Diode Forward Voltage	$I_F=6\text{A}$			2.0	V
t_f	Fall Time	$I_{CP}=5\text{A}$, $I_{B1}=1\text{A}$; $I_{B2}=-2\text{A}$			0.4	μs

www.iscsemi.cn

isc Silicon NPN Power Transistor

2SC4744

